

**IN THE CLAIMS**

The claims are now pending as follows:

1-21 (Cancelled)

--22. (Previously presented) An electronic device having a substantially consistent gate voltage and a saturation mobility  $\mu$ , in the range of about 0.001 to about 100 cm<sup>2</sup>/V.s.--

23. (Cancelled)

--24. (Currently Amended) A device comprising a substantially exclusive polycrystalline Si:H or a polycrystalline and amorphous Si:H layer, said device having a substantially consistent gate voltage and a saturation mobility lying in the range of about 0.001 to about 500 cm<sup>2</sup>/V.s.--

25-27 (Cancelled)

--28. (Previously presented) The electronic device of claim 22 which has a saturation mobility in the range of about 0.001 to about 10 cm<sup>2</sup>/V.s.--

--29. (Previously presented) The electronic device of claim 22 which has a saturation mobility in the range of between about 0.1 to about 1.00 cm<sup>2</sup>/V.s.--

--30. (Previously presented) The electronic device of claim 22 which is a transistor.--

--31. (Previously presented) The device comprising a substantially exclusive polycrystalline Si:H or a polycrystalline and amorphous Si:H layer of claim 24 wherein said device has a saturation mobility lying in the range of about 0.001 to about 500 cm<sup>2</sup>/V.s.

--32. (Previously presented) A device obtainable according to a process for providing a semiconducting device comprising the steps of depositing a semiconducting layer onto a substrate situated in a vessel by means of heating gas to a predetermined, dissociation temperature so that the gas dissociates into fractions, whereby those fractions subsequently